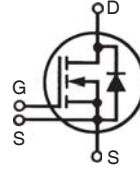


# Linear™ Power MOSFET IXTN3N250L

## w/Extended FBSOA

N-Channel Enhancement Mode

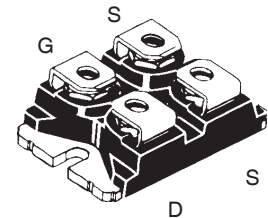


$$V_{DSS} = 2500V$$

$$I_{D25} = 3A$$

$$R_{DS(on)} \leq 10\Omega$$

miniBLOC, SOT-227  
 E153432



G = Gate      D = Drain  
 S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	2500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	2500	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	3	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	8	A
$P_D$	$T_C = 25^\circ C$	347	W
$T_J$		-55...+150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55...+150	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1$ second	3000	V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
<b>Weight</b>		30	g

### Features

- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- Designed for Linear Operation
- International Standard Package
- Guaranteed FBSOA at  $75^\circ C$

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Solid State Circuit Breakers
- Soft Start Controls
- Linear Amplifiers
- Programmable Loads
- Current Regulators

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	3.0		V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			10 $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 30\text{V}$ , $I_D = 1.5\text{A}$ , Note 1	0.6	1.0	1.4 S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		5400	pF
$C_{oss}$			260	pF
$C_{rss}$			63	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		44	ns
$t_r$			32	ns
$t_{d(off)}$			120	ns
$t_f$			160	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		230	nC
$Q_{gs}$			58	nC
$Q_{gd}$			100	nC
$R_{thJC}$				0.36 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 2\text{kV}$ , $I_D = 125\text{mA}$ , $T_C = 75^\circ\text{C}$ , $T_p = 5\text{s}$	250		W

### Source-Drain Diode

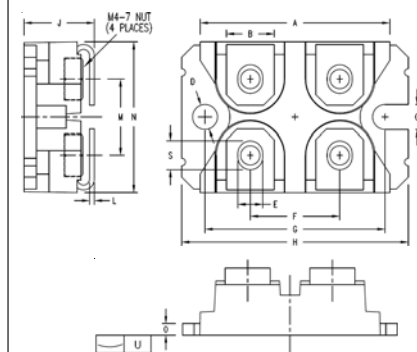
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			3 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			12 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 1.5\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$		370	ns
$I_{RM}$			18.4	A
$Q_{RM}$			3.4	$\mu\text{C}$

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

### SOT-227B miniBLOC (IXTN)

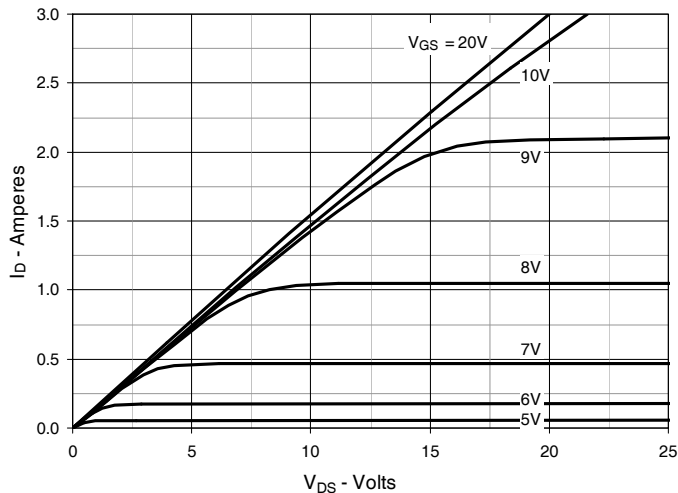


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

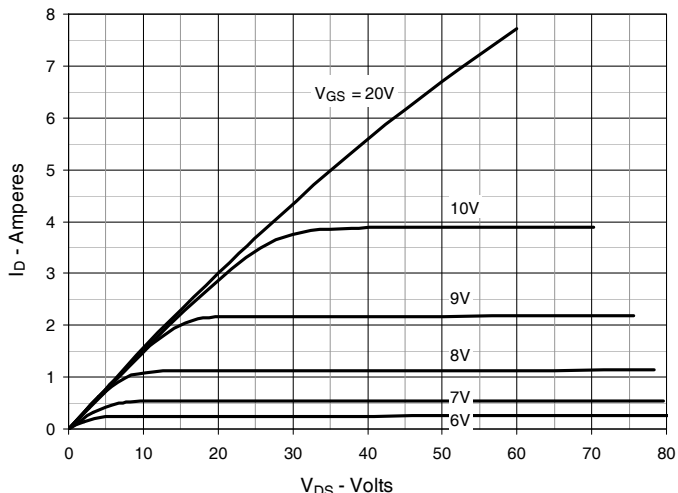
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

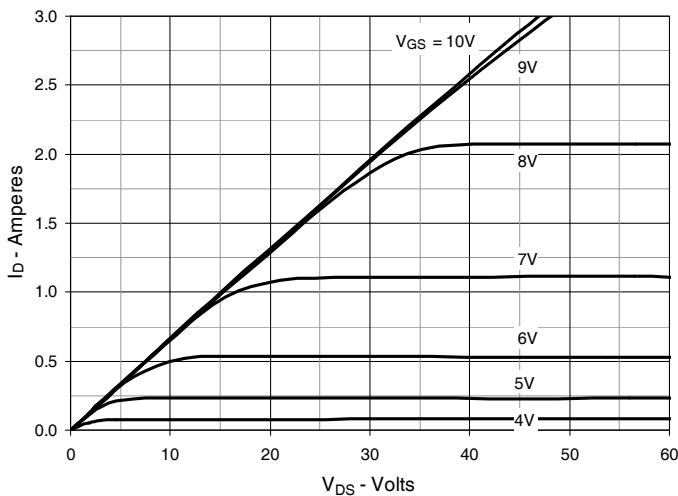
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



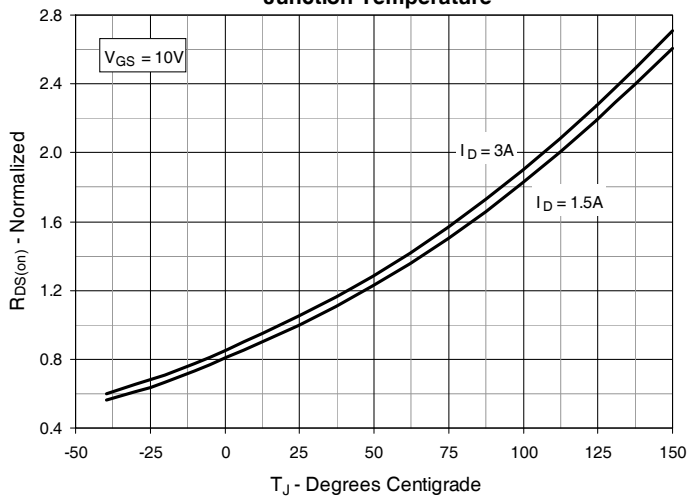
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



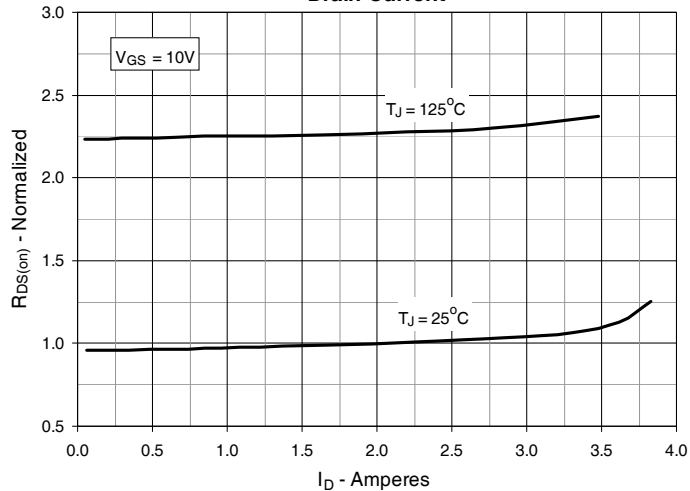
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



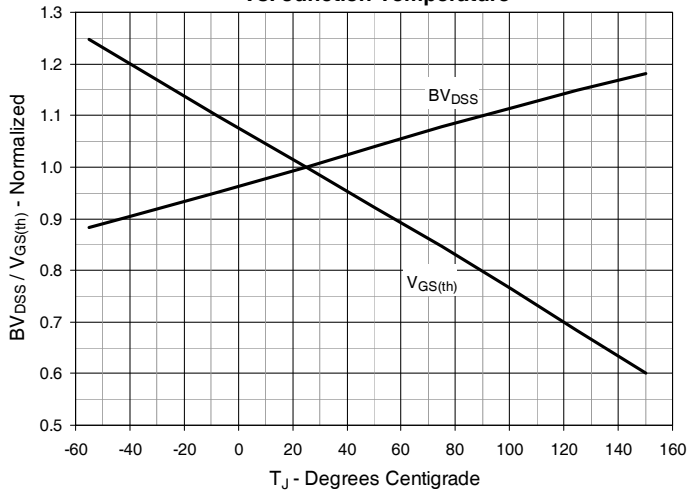
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 1.5\text{A}$  Value vs. Junction Temperature**



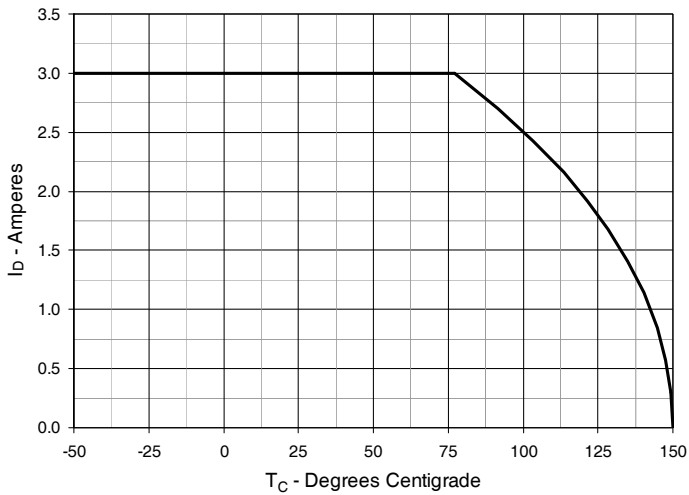
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 1.5\text{A}$  Value vs. Drain Current**



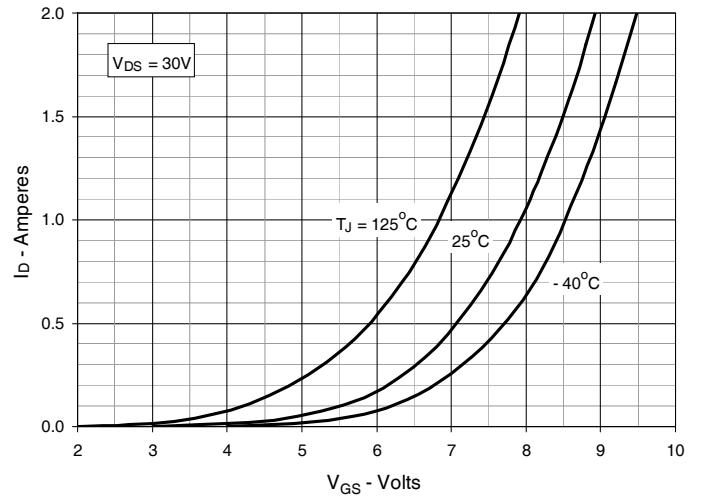
**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**



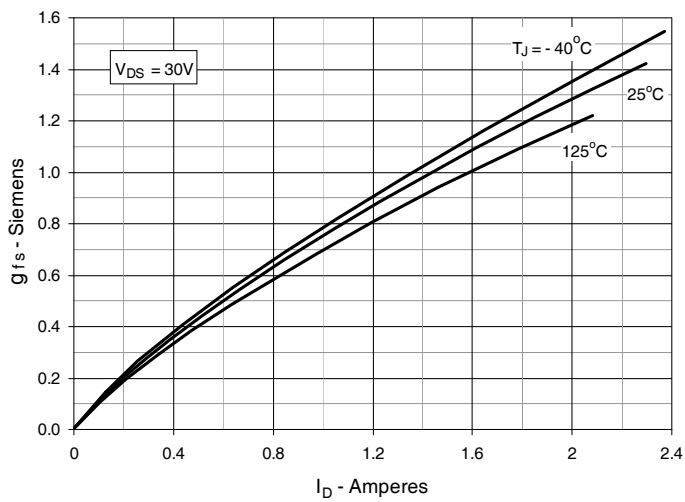
**Fig. 7. Maximum Drain Current vs. Case Temperature**



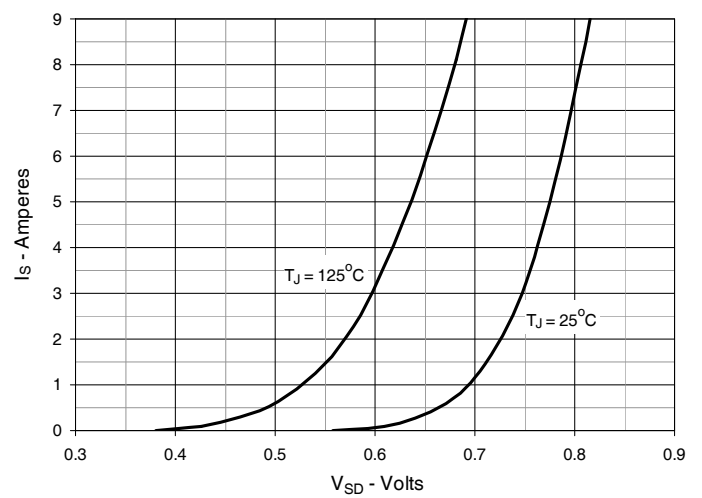
**Fig. 8. Input Admittance**



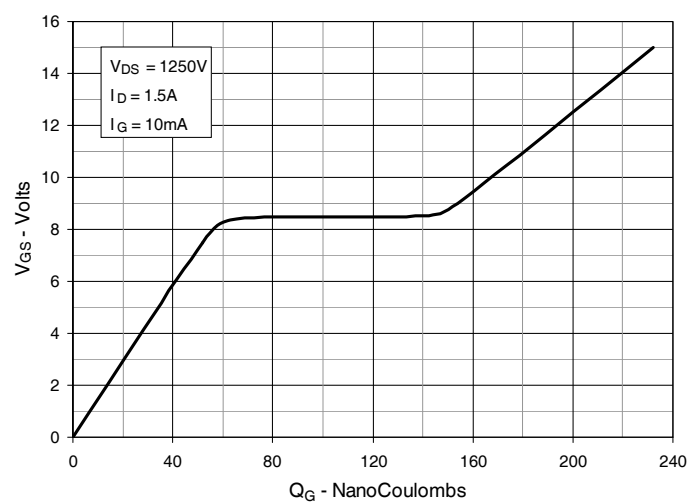
**Fig. 9. Transconductance**



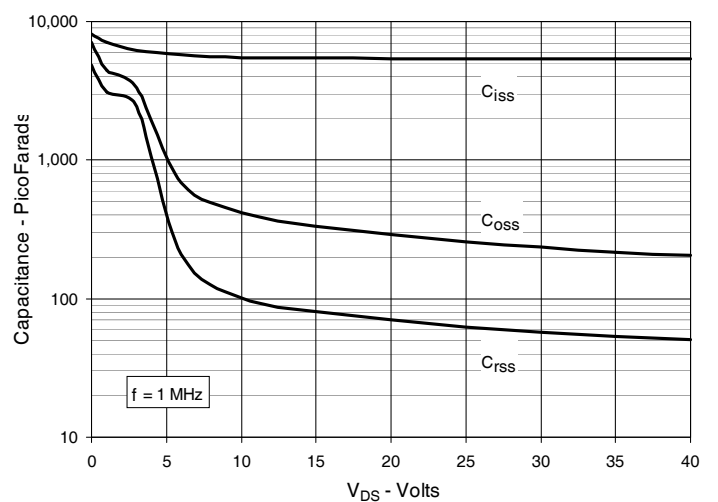
**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



**Fig. 11. Gate Charge**

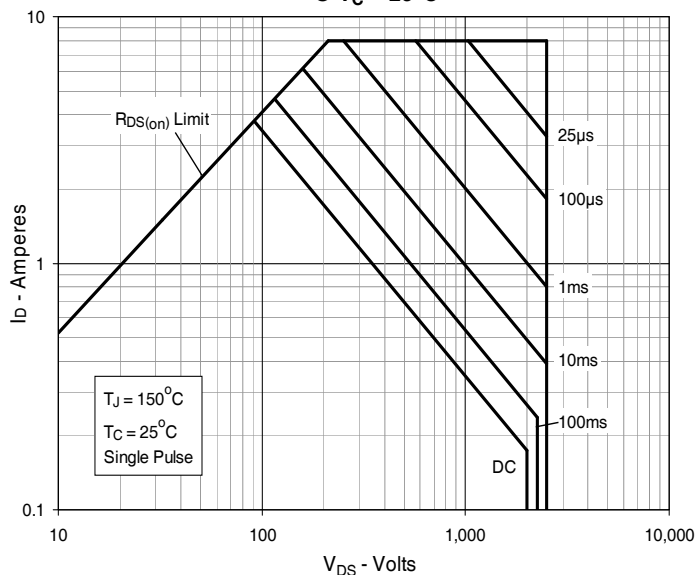


**Fig. 12. Capacitance**



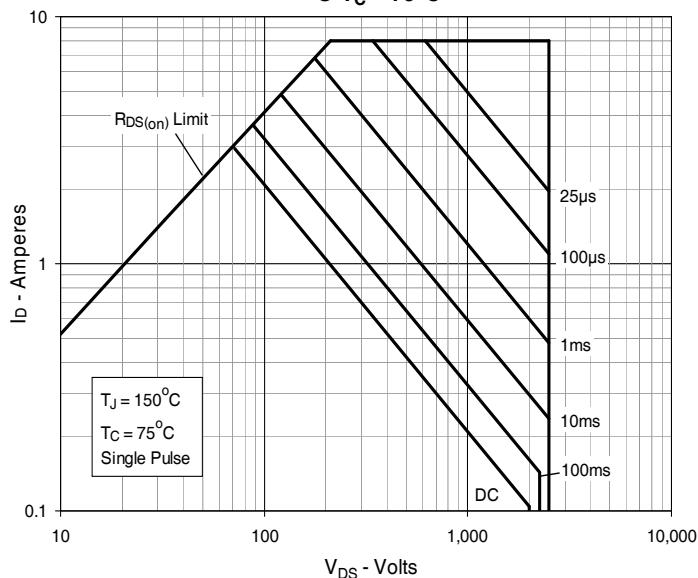
**Fig. 13. Forward-Bias Safe Operating Area**

@  $T_C = 25^\circ\text{C}$

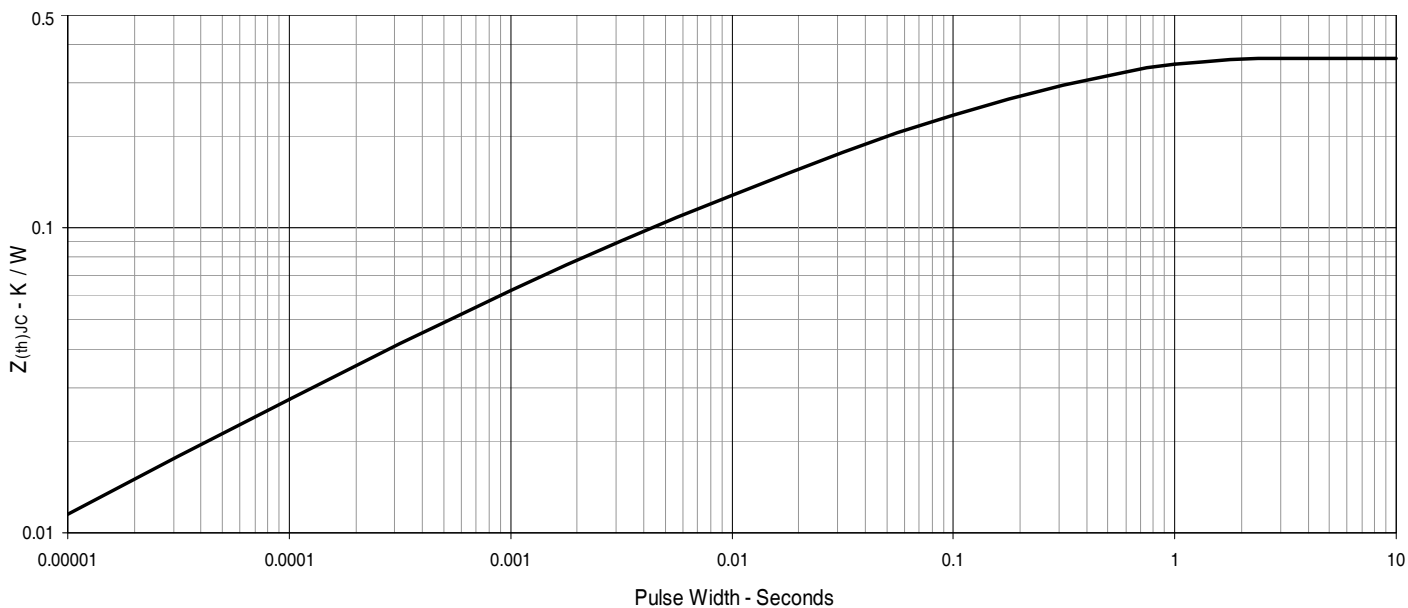


**Fig. 14. Forward-Bias Safe Operating Area**

@  $T_C = 75^\circ\text{C}$



**Fig. 15. Maximum Transient Thermal Impedance**





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